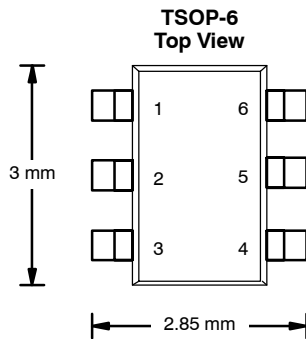


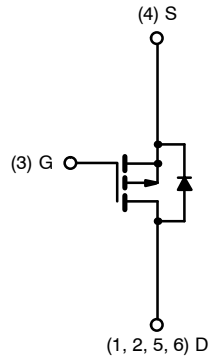
P-Channel 2.5-V (G-S) MOSFET

TrenchFET®
Power MOSFETs

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-20	0.090 @ $V_{GS} = -4.5$ V	-2.9
	0.130 @ $V_{GS} = -2.5$ V	-2.45



Ordering Information: Si3441BDV-T1
Si3441BDV-T1—E3 (Lead Free)
Marking Code: B1xxx



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	-20		V	
Gate-Source Voltage	V_{GS}	± 8			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	-2.9	-2.45	A
		$T_A = 70^\circ\text{C}$	-2.35	-1.95	
Pulsed Drain Current	I_{DM}	-16			
Continuous Diode Current (Diode Conduction) ^a	I_S	-1.0	-0.72		
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	1.25	0.86	W
		$T_A = 70^\circ\text{C}$	0.8	0.55	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	80	100	$^\circ\text{C/W}$
	Steady State		120	145	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	70	85	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>.

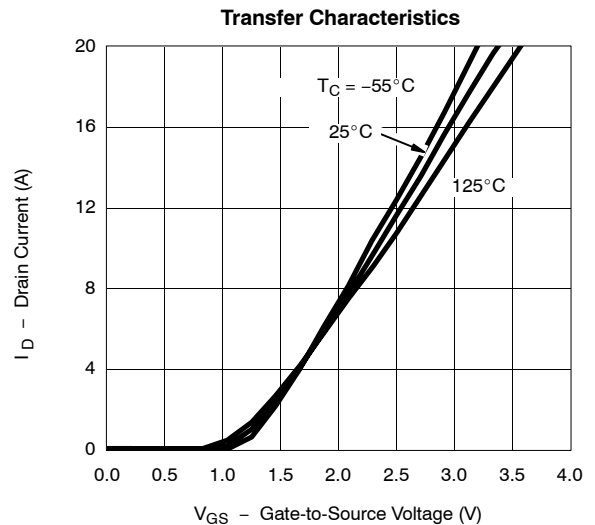
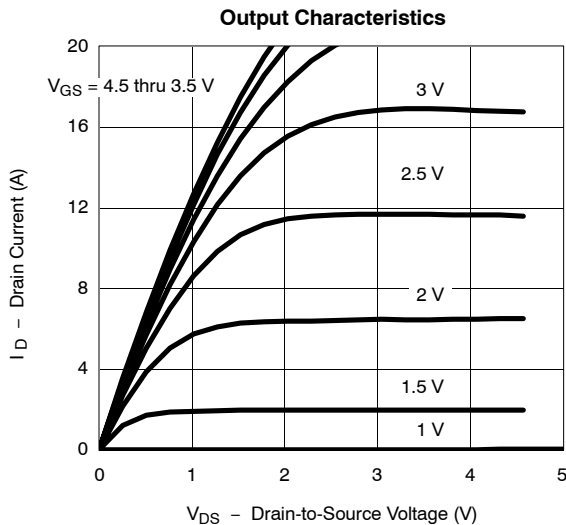


SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.45		-0.85	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -20 V, V _{GS} = 0 V, T _J = 70 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -4.5 V	-10			A
		V _{DS} = -5 V, V _{GS} = -2.5 V	-4			
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -3.3 A		0.070	0.090	Ω
		V _{GS} = -2.5 V, I _D = -2.9 A		0.098	0.130	
Forward Transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -3.3 A		8.0		S
Diode Forward Voltage ^a	V _{SD}	I _S = -1.6 A, V _{GS} = 0 V		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -3.3 A		5.2	8.0	nC
Gate-Source Charge	Q _{gs}			0.8		
Gate-Drain Charge	Q _{gd}			1.5		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -10 V, R _L = 10 Ω I _D ≅ -1.0 A, V _{GEN} = -4.5 V, R _g = 6 Ω		15	25	ns
Rise Time	t _r			55	85	
Turn-Off Delay Time	t _{d(off)}			30	45	
Fall Time	t _f			40	60	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = -1.6 A, di/dt = 100 A/μs		50	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

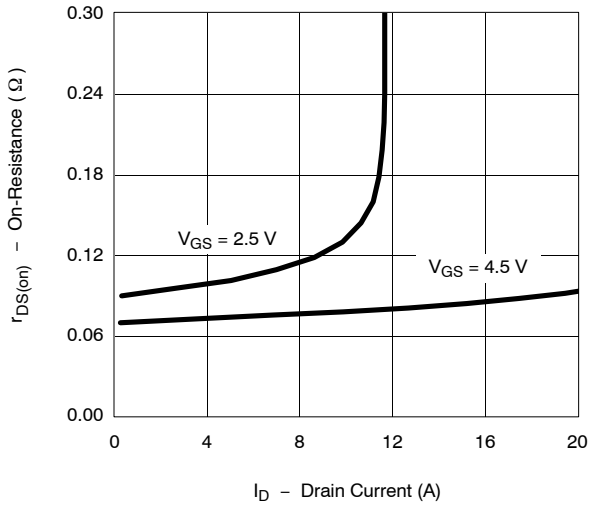
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



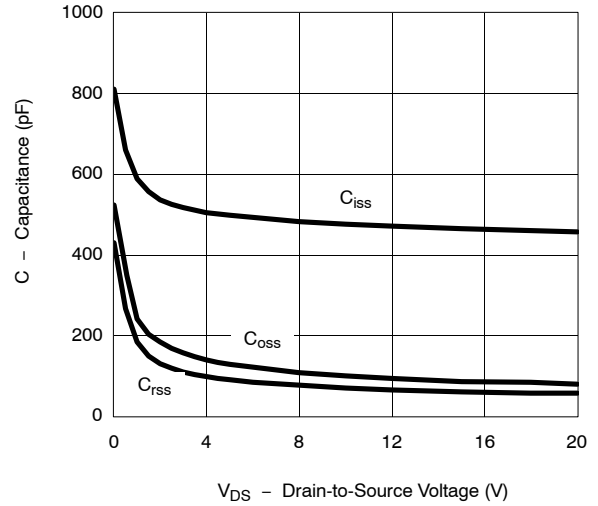


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

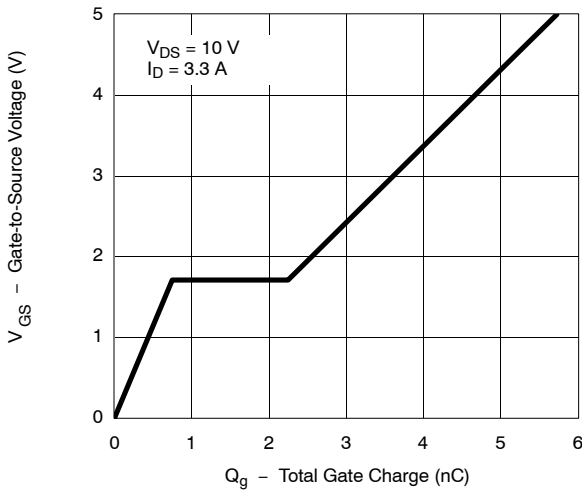
On-Resistance vs. Drain Current



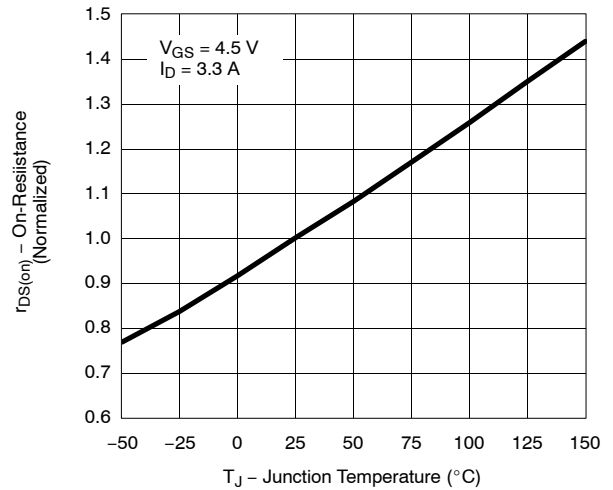
Capacitance



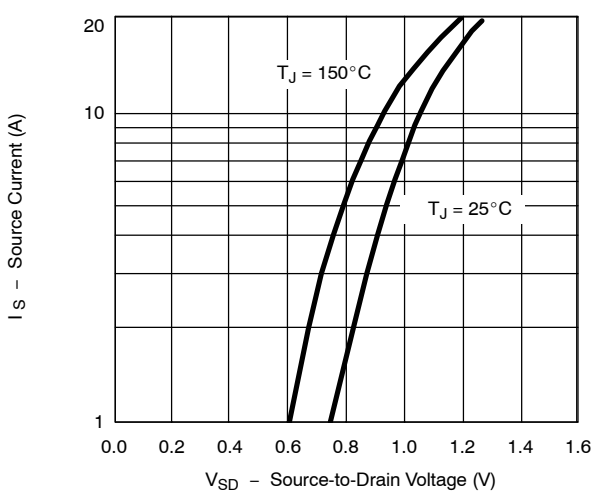
Gate Charge



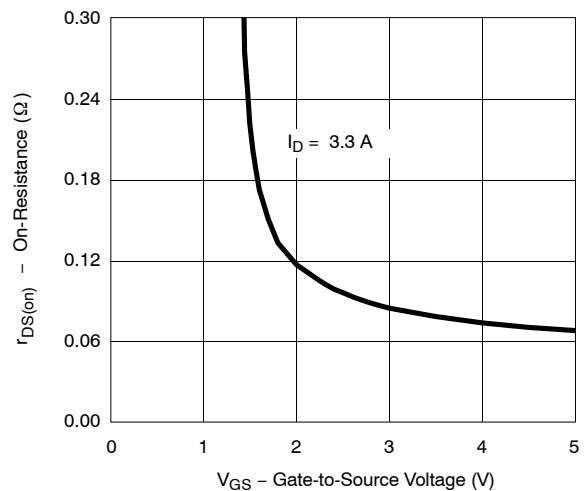
On-Resistance vs. Junction Temperature



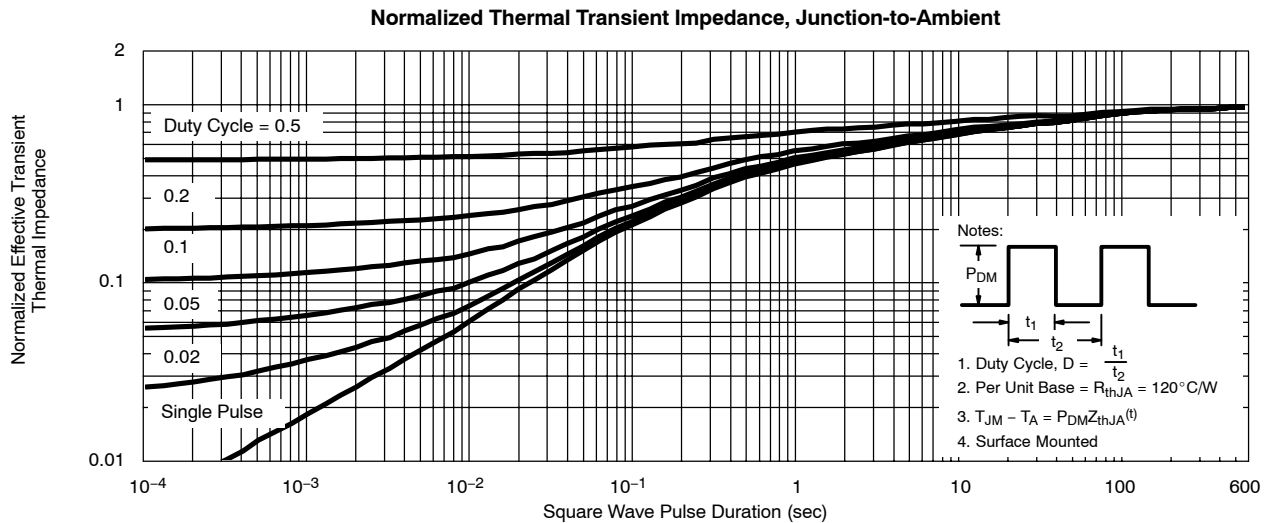
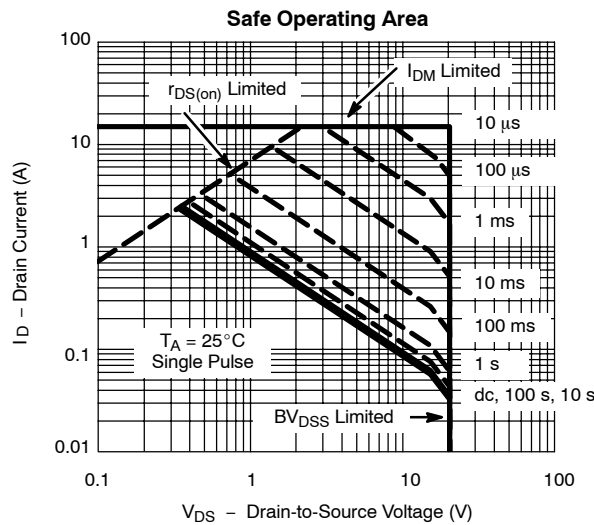
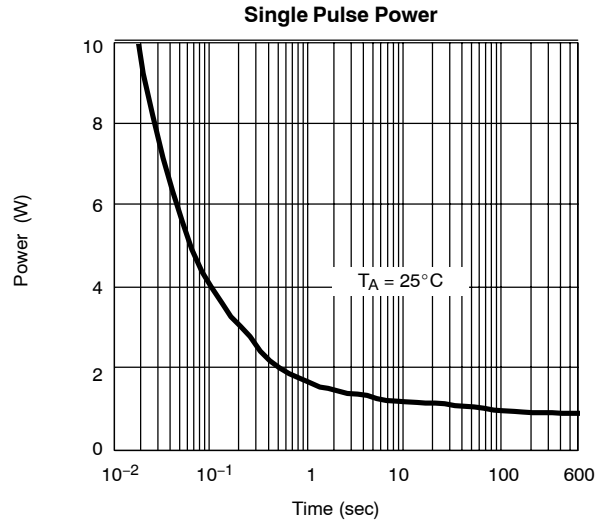
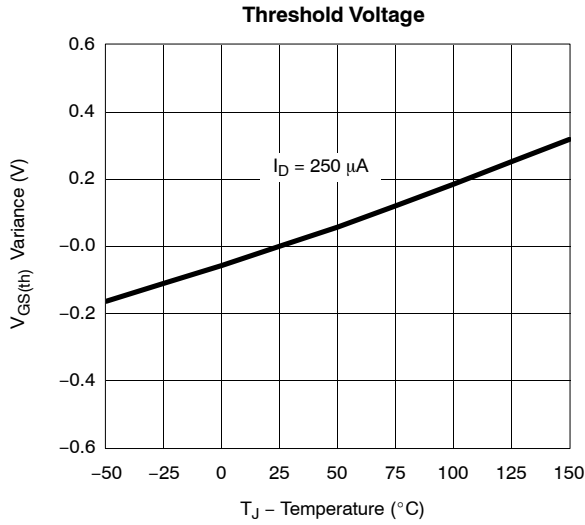
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

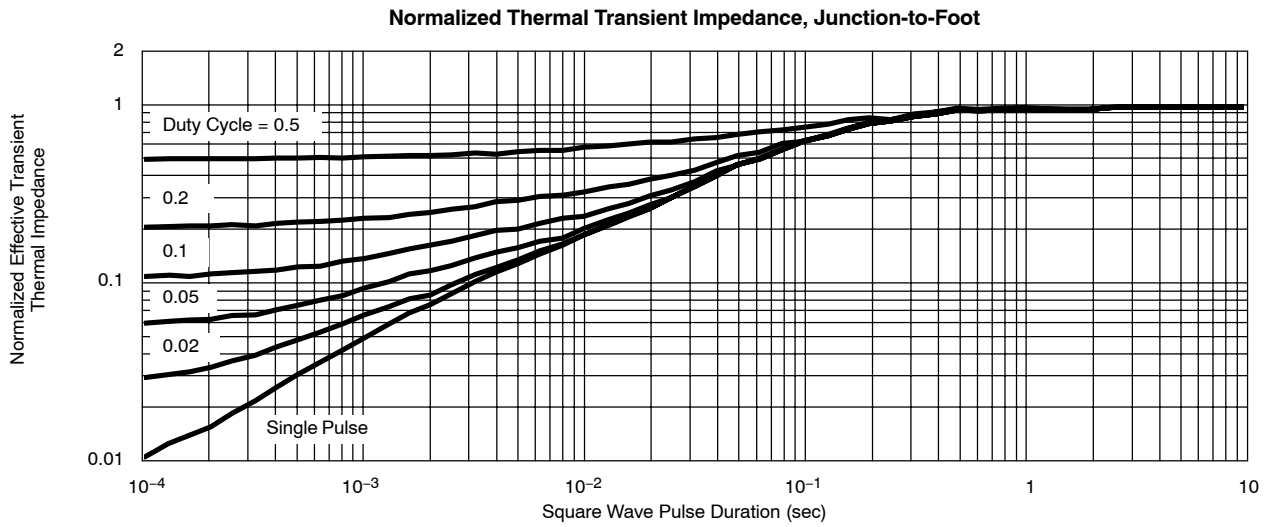


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





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